

# UFS Series N-Channel IGBT with Anti-Parallel Hyperfast Diode

60 A, 600 V

## HGTG30N60B3D

The HGTG30N60B3D is a MOS gated high voltage switching device combining the best features of MOSFETs and bipolar transistors. This device has the high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. The much lower on-state voltage drop varies only moderately between 25°C and 150°C. The IGBT used is the development type TA49170. The diode used in anti-parallel with the IGBT is the development type TA49053.

The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential, such as: AC and DC motor controls, power supplies and drivers for solenoids, relays and contactors.

Formerly Developmental Type TA49172.

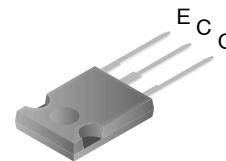
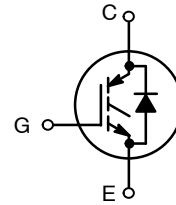
### Features

- 60 A, 600 V,  $T_C = 25^\circ\text{C}$
- 600 V Switching SOA Capability
- Typical Fall Time 90 ns at  $T_J = 150^\circ\text{C}$
- Short Circuit Rating
- Low Conduction Loss
- Hyperfast Anti-Parallel Diode
- This is a Pb-Free Device



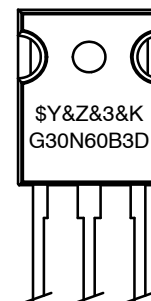
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TO-247-3LD SHORT LEAD  
CASE 340CK  
JEDEC STYLE

### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Numeric Date Code  
&K = Lot Code  
G30N60B3D = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

# HGTG30N60B3D

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise specified)

Parameter	Symbol	HGTG30N60B3D	Unit
Collector to Emitter Voltage	BV <sub>CES</sub>	600	V
Collector Current Continuous At T <sub>C</sub> = 25°C At T <sub>C</sub> = 110°C	I <sub>C25</sub> I <sub>C110</sub>	60 30	A A
Average Diode Forward Current at 110°C	I <sub>EC(AVG)</sub>	25	A
Collector Current Pulsed (Note 1)	I <sub>CM</sub>	220	A
Gate to Emitter Voltage Continuous	V <sub>GES</sub>	±20	V
Gate to Emitter Voltage Pulsed	V <sub>GEM</sub>	±30	V
Switching Safe Operating Area at T <sub>J</sub> = 150°C, (Figure 2)	SSOA	60 A at 600 V	
Power Dissipation Total at T <sub>C</sub> = 25°C	P <sub>D</sub>	208	W
Power Dissipation Derating T <sub>C</sub> > 25°C		1.67	W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C
Maximum Lead Temperature for Soldering	T <sub>L</sub>	260	°C
Short Circuit Withstand Time (Note 2) at V <sub>GE</sub> = 12 V	t <sub>SC</sub>	4	μs
Short Circuit Withstand Time (Note 2) at V <sub>GE</sub> = 10 V	t <sub>SC</sub>	10	μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse width limited by maximum junction temperature.
2. V<sub>CE(PK)</sub> = 360 V, T<sub>J</sub> = 125°C, R<sub>G</sub> = 3 Ω.

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
Collector to Emitter Breakdown Voltage	BV <sub>CES</sub>	I <sub>C</sub> = 250 μA, V <sub>GE</sub> = 0 V	600	-	-	V	
Collector to Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> = BV <sub>CES</sub>	T <sub>J</sub> = 25°C	-	-	250	μA
			T <sub>J</sub> = 150°C	-	-	3	mA
Collector to Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> = I <sub>C110</sub> , V <sub>GE</sub> = 15 V	T <sub>J</sub> = 25°C	-	1.45	1.9	V
			T <sub>J</sub> = 150°C	-	1.7	2.1	V
Gate to Emitter Threshold Voltage	V <sub>GE(TH)</sub>	I <sub>C</sub> = 250 μA, V <sub>CE</sub> = V <sub>GE</sub>	4.2	5	6	V	
Gate to Emitter Leakage Current	I <sub>GES</sub>	V <sub>GE</sub> = ±20 V	-	-	±250	nA	
Switching SOA	SSOA	T <sub>J</sub> = 150°C, R <sub>G</sub> = 3 Ω, V <sub>GE</sub> = 15 V, L = 100 μH,	V <sub>CE(PK)</sub> = 480 V	200	-	-	A
			V <sub>CE(PK)</sub> = 600 V	60	-	-	A
Gate to Emitter Plateau Voltage	V <sub>GEP</sub>	I <sub>C</sub> = I <sub>C110</sub> , V <sub>CE</sub> = 0.5 BV <sub>CES</sub>	-	7.2	-	V	
On-State Gate Charge	Q <sub>G(ON)</sub>	I <sub>C</sub> = I <sub>C110</sub> , V <sub>CE</sub> = 0.5 BV <sub>CES</sub>	V <sub>GE</sub> = 15 V	-	170	190	nC
			V <sub>GE</sub> = 20 V	-	230	250	nC
Current Turn-On Delay Time	t <sub>d(ON)I</sub>	IGBT and Diode at T <sub>J</sub> = 25°C, I <sub>CE</sub> = I <sub>C110</sub> , V <sub>CE</sub> = 0.8 BV <sub>CES</sub> , V <sub>GE</sub> = 15 V, R <sub>G</sub> = 3 Ω, L = 1 mH, Test Circuit (Figure 19)	-	36	-	ns	
Current Rise Time	t <sub>ri</sub>		-	25	-	ns	
Current Turn-Off Delay Time	t <sub>d(OFF)I</sub>		-	137	-	ns	
Current Fall Time	t <sub>fi</sub>		-	58	-	ns	
Turn-On Energy	E <sub>ON</sub>		-	550	800	μJ	
Turn-Off Energy (Note 3)	E <sub>OFF</sub>		-	680	900	μJ	
Current Turn-On Delay Time	t <sub>d(ON)I</sub>		IGBT and Diode at T <sub>J</sub> = 150°C, I <sub>CE</sub> = I <sub>C110</sub> , V <sub>CE</sub> = 0.8 BV <sub>CES</sub> , V <sub>GE</sub> = 15 V, R <sub>G</sub> = 3 Ω, L = 1 mH, Test Circuit (Figure 19)	-	32	-	ns
Current Rise Time	t <sub>ri</sub>			-	24	-	ns
Current Turn-Off Delay Time	t <sub>d(OFF)I</sub>	-		275	320	ns	
Current Fall Time	t <sub>fi</sub>	-		90	150	ns	
Turn-On Energy	E <sub>ON</sub>	-		1300	1550	μJ	
Turn-Off Energy (Note 3)	E <sub>OFF</sub>	-		1600	1900	μJ	
Diode Forward Voltage	V <sub>EC</sub>	I <sub>EC</sub> = 30 A		-	1.95	2.5	V

# HGTG30N60B3D

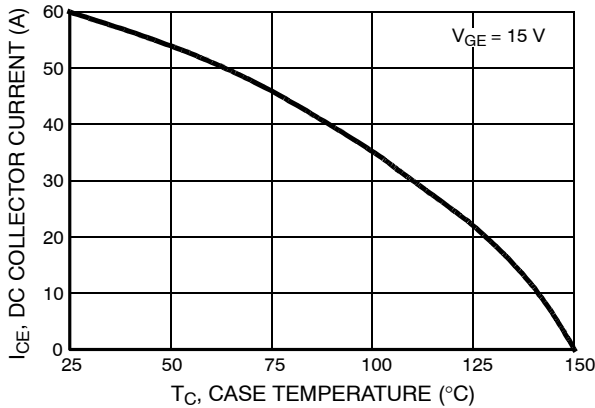
## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Diode Reverse Recovery Time	$t_{rr}$	$I_{EC} = 1\text{ A}, dI_{EC}/dt = 200\text{ A}/\mu\text{s}$	–	32	40	ns
		$I_{EC} = 30\text{ A}, dI_{EC}/dt = 200\text{ A}/\mu\text{s}$	–	45	55	ns
Thermal Resistance Junction To Case	$R_{\theta JC}$	IGBT	–	–	0.6	$^\circ\text{C}/\text{W}$
		Diode	–	–	1.3	$^\circ\text{C}/\text{W}$

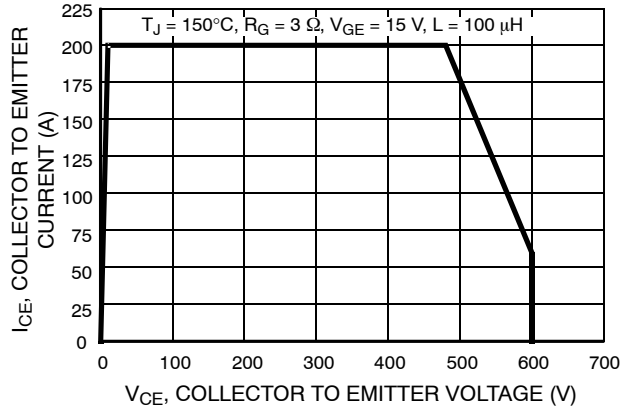
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Turn-Off Energy Loss ( $E_{OFF}$ ) is defined as the integral of the instantaneous power loss starting at the trailing edge of the input pulse and ending at the point where the collector current equals zero ( $I_{CE} = 0\text{ A}$ ). All devices were tested per JEDEC Standard No. 24-1 Method for Measurement of Power Device Turn-Off Switching Loss. This test method produces the true total Turn-Off Energy Loss.

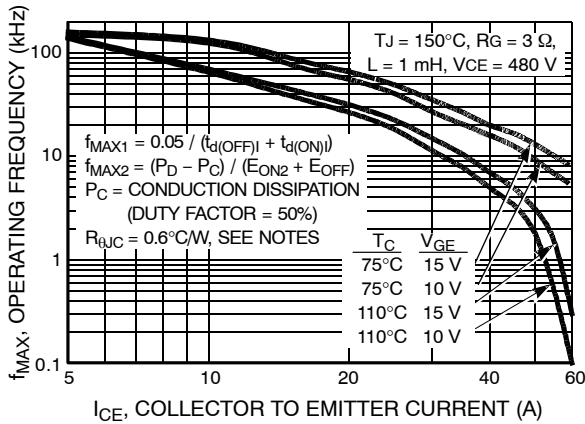
## TYPICAL PERFORMANCE CURVES (unless otherwise specified)



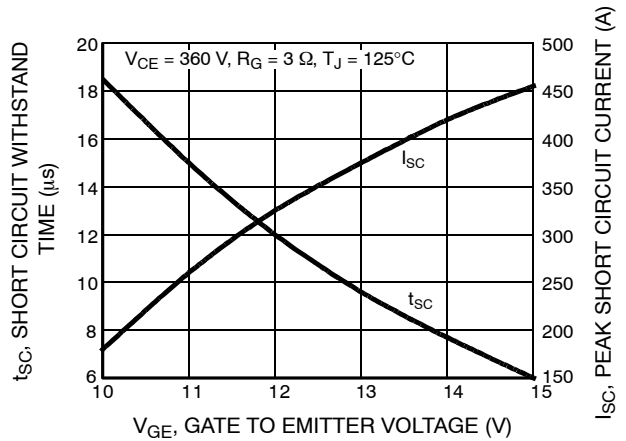
**Figure 1. DC COLLECTOR CURRENT vs. CASE TEMPERATURE**



**Figure 2. MINIMUM SWITCHING SAFE OPERATING AREA**



**Figure 3. OPERATING FREQUENCY vs. COLLECTOR TO EMITTER CURRENT**



**Figure 4. SHORT CIRCUIT WITHSTAND TIME**

TYPICAL PERFORMANCE CURVES (unless otherwise specified) (continued)

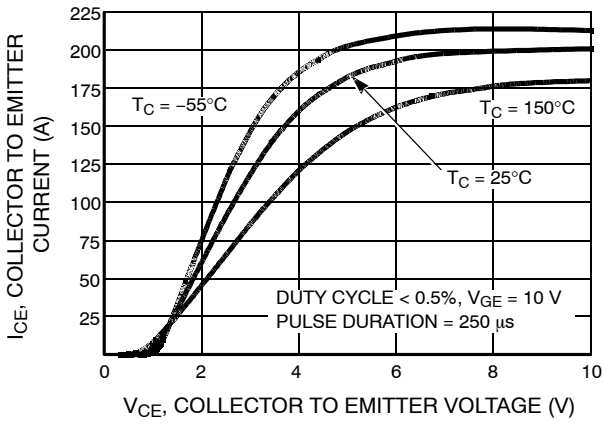


Figure 5. COLLECTOR TO EMITTER ON-STATE VOLTAGE

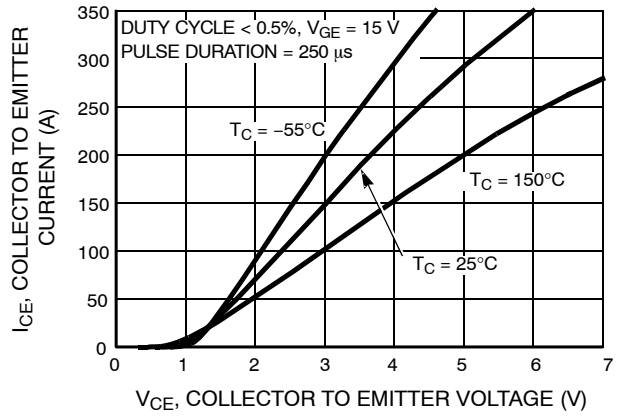


Figure 6. COLLECTOR TO EMITTER ON-STATE VOLTAGE

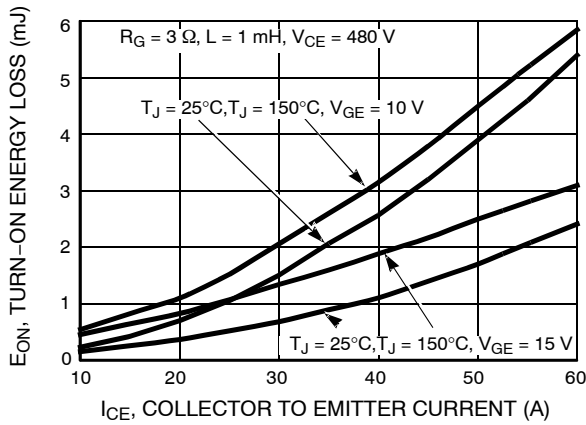


Figure 7. TURN-ON ENERGY LOSS vs. COLLECTOR TO EMITTER CURRENT

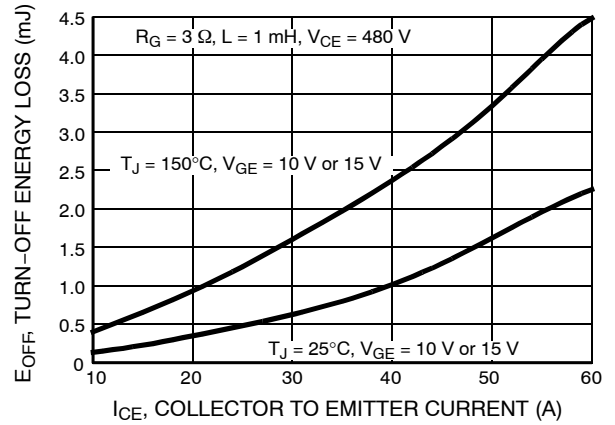


Figure 8. TURN-OFF ENERGY LOSS vs. COLLECTOR TO EMITTER CURRENT

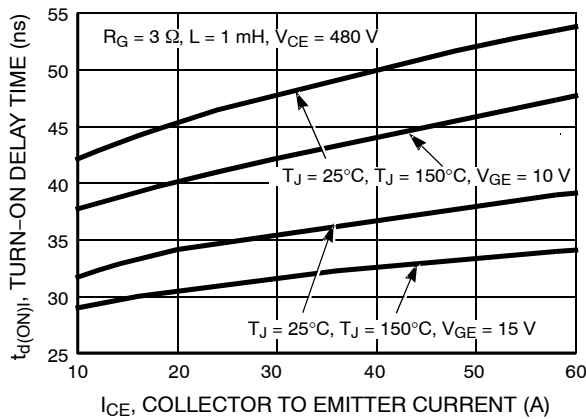


Figure 9. TURN-ON DELAY TIME vs. COLLECTOR TO EMITTER CURRENT

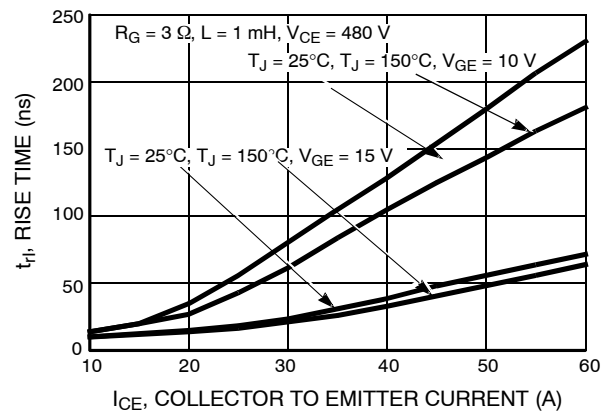
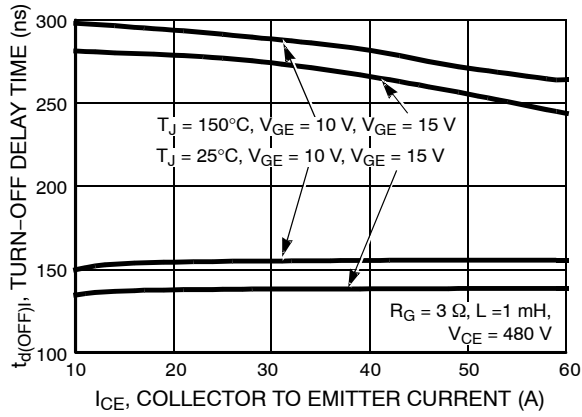


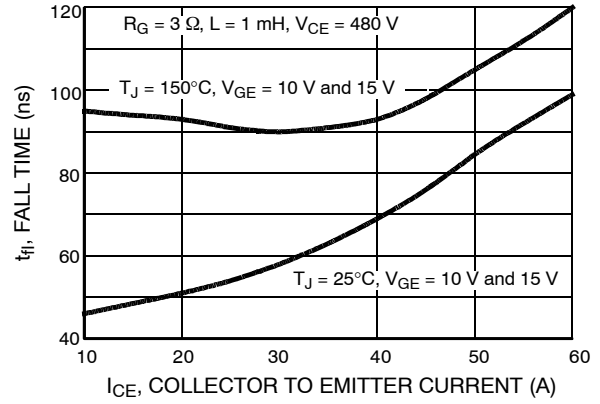
Figure 10. TURN-ON RISE TIME vs. COLLECTOR TO EMITTER CURRENT

# HGTG30N60B3D

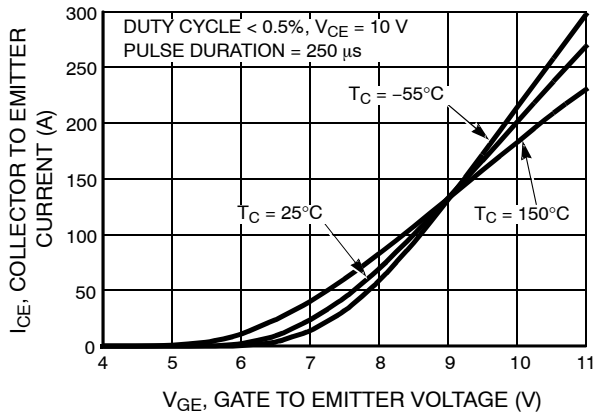
## TYPICAL PERFORMANCE CURVES (unless otherwise specified) (continued)



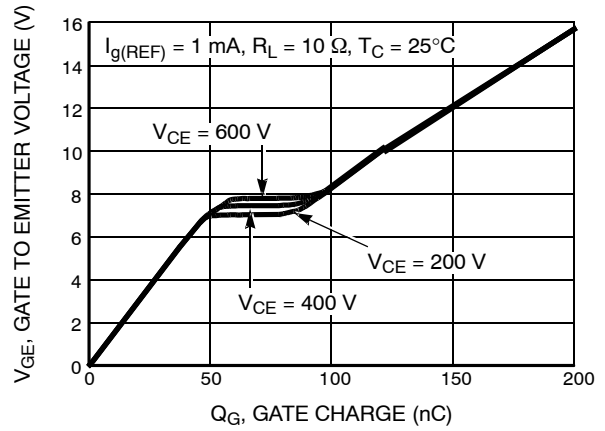
**Figure 11. TURN-OFF DELAY TIME vs. COLLECTOR TO EMITTER CURRENT**



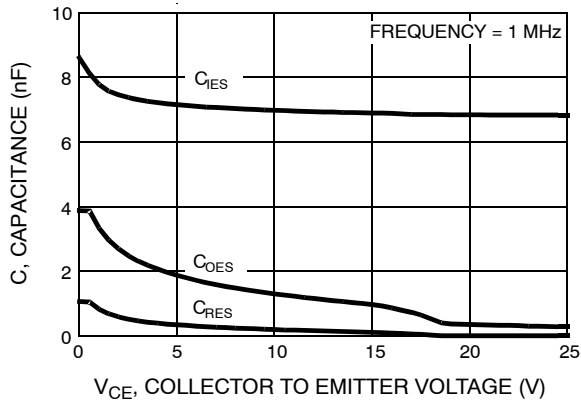
**Figure 12. FALL TIME vs. COLLECTOR TO EMITTER CURRENT**



**Figure 13. TRANSFER CHARACTERISTIC**



**Figure 14. GATE CHARGE WAVEFORMS**



**Figure 15. CAPACITANCE vs. COLLECTOR TO EMITTER VOLTAGE**

# HGTG30N60B3D

## TYPICAL PERFORMANCE CURVES (unless otherwise specified) (continued)

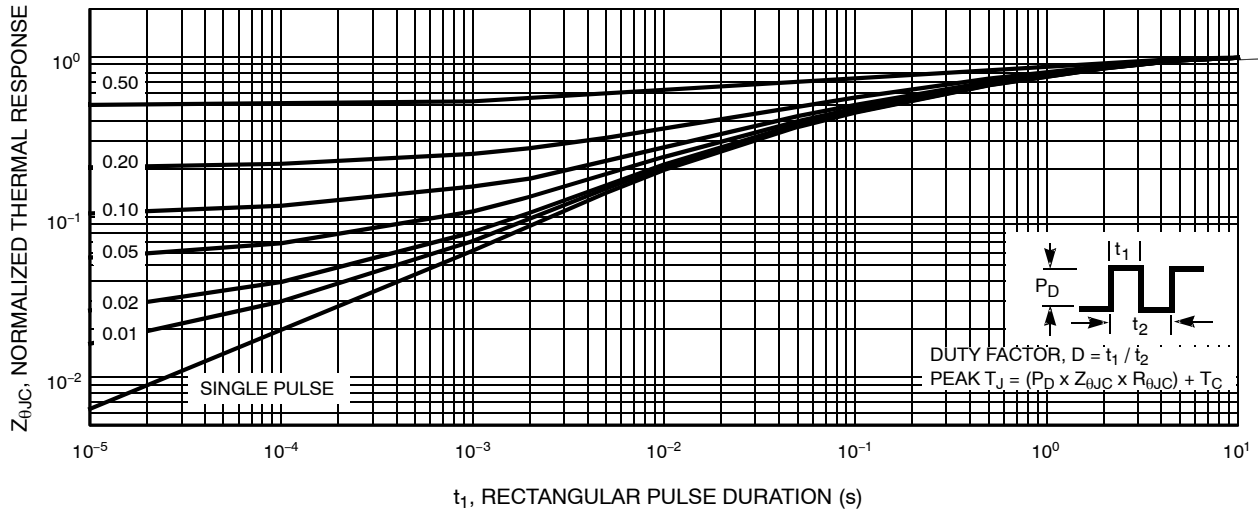


Figure 16. NORMALIZED TRANSIENT THERMAL RESPONSE, JUNCTION TO CASE

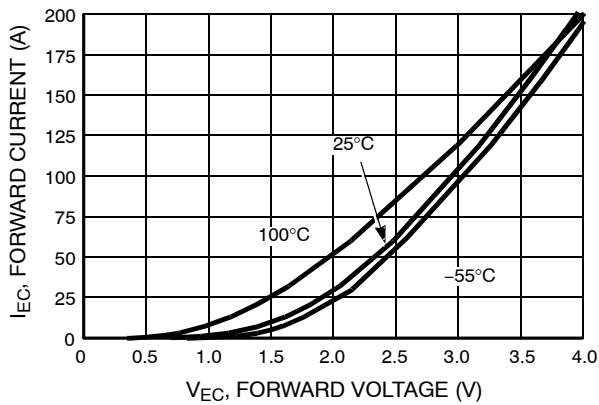


Figure 17. DIODE FORWARD CURRENT vs. FORWARD VOLTAGE DROP

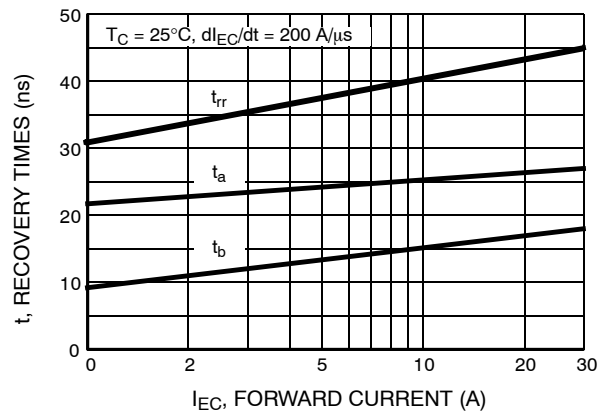


Figure 18. RECOVERY TIMES vs. FORWARD CURRENT

## TEST CIRCUIT AND WAVEFORMS

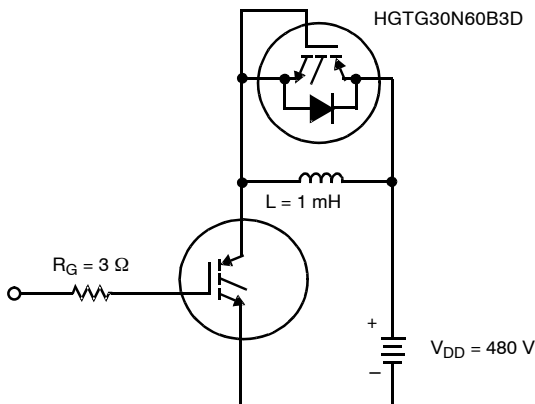


Figure 19. INDUCTIVE SWITCHING TEST CIRCUIT

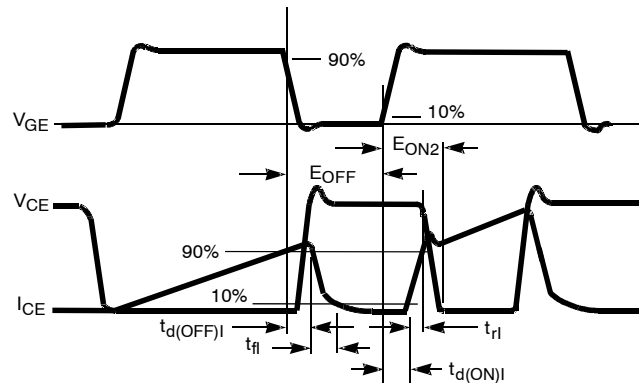


Figure 20. SWITCHING TEST WAVEFORMS

# HGTG30N60B3D

## HANDLING PRECAUTIONS FOR IGBTs

Insulated Gate Bipolar Transistors are susceptible to gate-insulation damage by the electrostatic discharge of energy through the devices. When handling these devices, care should be exercised to assure that the static charge built in the handler's body capacitance is not discharged through the device. With proper handling and application procedures, however, IGBTs are currently being extensively used in production by numerous equipment manufacturers in military, industrial and consumer applications, with virtually no damage problems due to electrostatic discharge. IGBTs can be handled safely if the following basic precautions are taken:

1. Prior to assembly into a circuit, all leads should be kept shorted together either by the use of metal shorting springs or by the insertion into conductive material such as "ECCOSORB<sup>TM</sup> LD26" or equivalent.
2. When devices are removed by hand from their carriers, the hand being used should be grounded by any suitable means – for example, with a metallic wristband.
3. Tips of soldering irons should be grounded.
4. Devices should never be inserted into or removed from circuits with power on.
5. Gate Voltage Rating – Never exceed the gate-voltage rating of  $V_{GEM}$ . Exceeding the rated  $V_{GE}$  can result in permanent damage to the oxide layer in the gate region.
6. Gate Termination – The gates of these devices are essentially capacitors. Circuits that leave the gate open-circuited or floating should be avoided. These conditions can result in turn-on of the device due to voltage buildup on the input capacitor due to leakage currents or pickup.

7. Gate Protection – These devices do not have an internal monolithic Zener diode from gate to emitter. If gate protection is required an external Zener is recommended.

## OPERATING FREQUENCY INFORMATION

Operating frequency information for a typical device (Figure 3) is presented as a guide for estimating device performance for a specific application. Other typical frequency vs collector current ( $I_{CE}$ ) plots are possible using the information shown for a typical unit in Figures 5, 6, 7, 8, 9 and 11. The operating frequency plot (Figure 3) of a typical device shows  $f_{MAX1}$  or  $f_{MAX2}$ ; whichever is smaller at each point. The information is based on measurements of a typical device and is bounded by the maximum rated junction temperature.

$f_{MAX1}$  is defined by  $f_{MAX1} = 0.05 / (t_{d(OFF)I} + t_{d(ON)I})$ . Deadtime (the denominator) has been arbitrarily held to 10% of the on-state time for a 50% duty factor. Other definitions are possible.  $t_{d(OFF)I}$  and  $t_{d(ON)I}$  are defined in Figure 20. Device turn-off delay can establish an additional frequency limiting condition for an application other than  $T_{JM}$ .  $t_{d(OFF)I}$  is important when controlling output ripple under a lightly loaded condition.

$f_{MAX2}$  is defined by  $f_{MAX2} = (P_D - P_C) / (E_{OFF} + E_{ON})$ . The allowable dissipation ( $P_D$ ) is defined by  $P_D = (T_{JM} - T_C) / R_{\theta JC}$ . The sum of device switching and conduction losses must not exceed  $P_D$ . A 50% duty factor was used (Figure 3) and the conduction losses ( $P_C$ ) are approximated by  $P_C = (V_{CE} \times I_{CE}) / 2$ .

$E_{ON}$  and  $E_{OFF}$  are defined in the switching waveforms shown in Figure 20.  $E_{ON}$  is the integral of the instantaneous power loss ( $I_{CE} \times V_{CE}$ ) during turn-on and  $E_{OFF}$  is the integral of the instantaneous power loss ( $I_{CE} \times V_{CE}$ ) during turn-off. All tail losses are included in the calculation for  $E_{OFF}$ ; i.e., the collector current equals zero ( $I_{CE} = 0$ ).

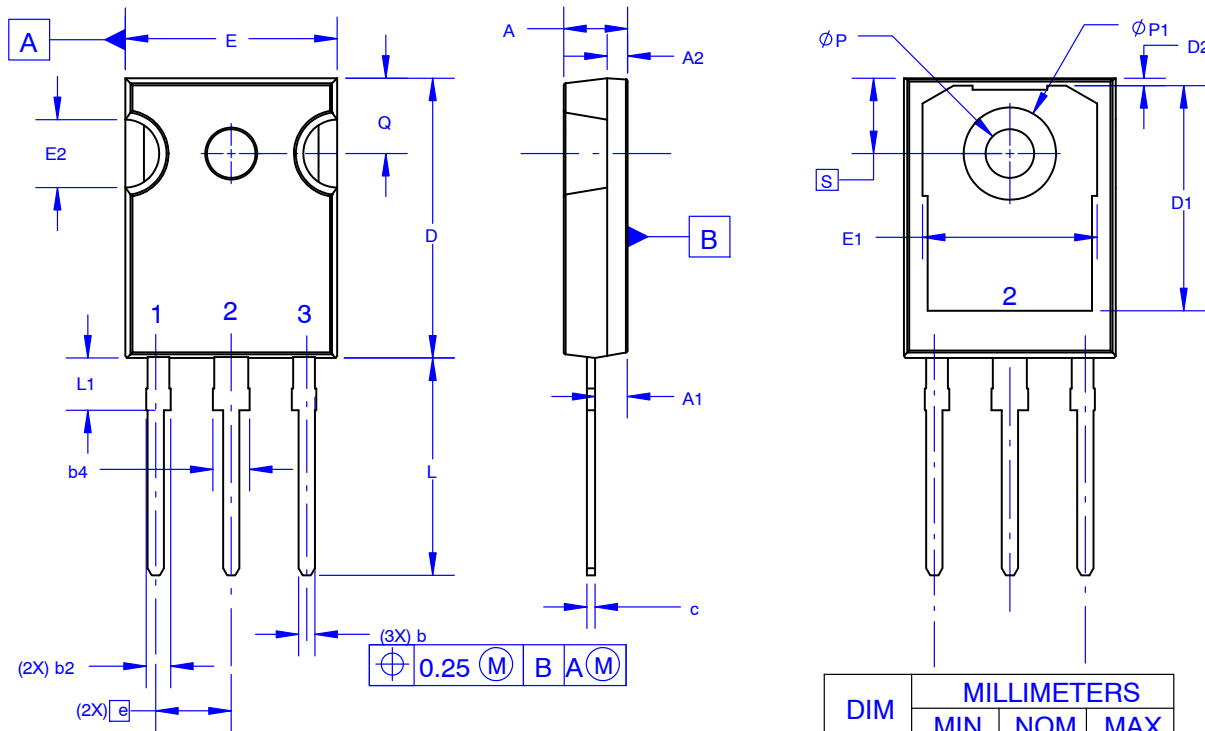
## ORDERING INFORMATION

Part Number	Package	Brand	Shipping <sup>†</sup>
HGTG30N60B3D	TO-247	G30N60B3D	450 Units / Tube

NOTE: When ordering, use the entire part number.

**TO-247-3LD SHORT LEAD**  
**CASE 340CK**  
**ISSUE A**

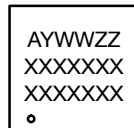
DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

**GENERIC MARKING DIAGRAM\***



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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<b>DESCRIPTION:</b>	<b>TO-247-3LD SHORT LEAD</b>	<b>PAGE 1 OF 1</b>

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